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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Application Number 10/028001
Filing Date 20, 2002
First Named Inventor Forbes, Leonard
Group Art Unit 2818
Examiner Name Unknown

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Attorney Docket No: 01303.035US1

US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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TH	US-4780424	10/25/1988	Holler, Mark A	437	29	09/28/1987
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Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Substitute Disclosure Statement Form (PTO-1449)

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